Program: BE Electronics & Telecommunication Engineering Curriculum Scheme: Rev2016

Examination: Third Year Semester VI

Course Code: ECCDLO6021 and Course Name: Digital VLSI design

Time: 1 hour Max. Marks: 50

Note to the students:- All the Questions are compulsory and carry equal marks.

	What will be the output, When both nMOS and pMOS transistors of CMOS logic		
Q1.	design are in OFF condition?		
Q1.	design are in OTT condition:		
Option A:	1 or Vdd or HIGH state		
Option B:	0 or ground or LOW state		
Option C:	High impedance or floating(Z)		
Option D:	Crowbarred or Contention(X)		
0.2	Which region n transistor operates in Pseudo-nMOS logic ?		
Q2.	The state of the s		
Option A:	cut off region		
Option B:	saturation region		
Option C:	resistive region		
Option D:	non saturation region		
Q3.	Which memory is volatile?		
Option A:	PROM		
Option B:	SRAM		
Option C:	ROM		
Option D:	PROM		
	A full CMOS SRAM cell has		
Q4.	A full CMOS SKAM cell flas		
Option A:	8T		
Option B:	6T		
Option C:	4T		
Option D:	2T		
	Pasad on how hinery information is antered or shifted out, shift registers are		
Q5.	Based on how binary information is entered or shifted out, shift registers are classified into categories.		
Option A:	2-Two		
Option B:	3-Three		
Option C:	4- Four		
Option D:	5- Five		

Q6.	In the adder, sum is stored in			
Option A:	series			
Option B:	cascade			
Option C:	parallel			
Option D:	1			
Option D.	Togasters .			
Q7.	Scaling a supply voltage helps to reduced			
Option A:	Crosstalk			
Option B:	Power			
Option C:	Delay			
Option D:	Speed			
Q8.	Power supply variation in the clock distribution causes a			
Option A:	Jitter			
Option B:	Skew			
Option C:	Slack			
Option D:	ESD			
Q9.	In FPGA, vertical and horizontal directions are separated by			
Option A:	A line			
Option B:	A channel			
Option C:	A strobe			
Option D:	A flipflop			
Q10.	A PLA is similar to a ROM in concept except that			
Option A:	It hasn't capability to read only			
Option B:	It hasn't capability to read or write operation			
Option C:	It doesn't provide full decoding to the variables			
Option D:	It hasn't capability to write only			
Q11.	Which of the following doesn't belongs to RTL design method?			
Option A:	Capture the HLSM			
Option B:	Create and connect data path to controller			
Option C:	Derive the controller's FSM			
Option D:	Disconnecting all controller Inputs and outputs			

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Q12.	It is not possible to use range with types in VHDL			
Option A:	Integer			
Option B:	BIT_VECTOR			
Option C:	STD_LOGIC			
Option D:	Natural Natural			
option D.	T (diction)			
Q13.	Which of the following HDLs are IEEE standard			
Option A:	VHDL and Verilog			
Option B:	C and C++			
Option C:	Altera and XILINX			
Option D:	Quartus and Maxplus II			
opnon 2 ·	Quantum min 112m.plus 11			
Q14.	For realization of given expression Z=Bar(A+BC) means $Z=\overline{A+BC}$ using Pseudo N-mos design style, how many numbers of nMOS and pMOS transistors required respectively?			
Option A:	nMOS=3 and pMOS=1			
Option B:	nMOS=3 and pMOS=3			
Option C:	nMOS=1 and pMOS=3			
Option D:	nMOS=1 and pMOS=1			
Q15.	In NOR type flash memory, each cell has one end is connected to			
Option A:	Source			
Option B:	Drain			
Option C:	Gate			
Option D:	Ground			
Q16.	What is ripple carry adder?			
Option A:	The carry output of the lower order stage is connected to the carry input of the next higher order stage			
Option B:	The carry input of the lower order stage is connected to the carry output of the next higher order stage			
Option C:	The carry output of the higher order stage is connected to the carry input of the next lower order stage			
Option D:	The carry input of the higher order stage is connected to the carry output of the lower order stage			

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Examination 2020 under cluster 4 (PCE)

	A Barrel Shifter is abased digital circuit.		
Q17.	A Darret Stiffter is abased digital circuit.		
Option A:	Encoder		
Option B:	Decoder		
Option C:	Buffer		
Option D:	Multiplexer		
Q18.	ESD protection is carried out by using		
Option A:	Transistor		
Option B:	Clamping Diode		
Option C:	Zener diode		
Option D:	Diode		
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Q19.	PLA contains		
Option A:	AND and OR arrays		
Option B:	NAND and OR arrays		
Option C:	NOT and AND arrays		
Option D:	NOR and OR arrays		
Q20.	Which of the following are common between HLSMs and FSMs?		
Option A:	Transitions happen at the edge of a clock		
Option B:	They have external complex data		
Option C:	Transitions happen at the Level of a clock		
Option D:	They don't have external complex data		
Q21.	The circuit of the given figure is CMOS implementation of		
Ontion A:	alcaled NAND based SD latab circuit		
Option A: Option B:	clocked NAND-based SR latch circuit. clocked NOR-based SR latch circuit.		
Option C:	clocked NOR-based SR latch circuit.		
Option C. Option D:	clocked XNOR-based SR latch circuit.		
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Q22.	In CMOS SRAM static power dissipation is low due to	
Option A:	moderate leakage current	
Option B:	large leakage current	
Option C:	small leakage current	
Option D:	no leakage current	
Q23.	Adder using technology can be used for speed improvement.	
Option A:	CMOS	
Option B:	BiCMOS	
Option C:	nMOS	
Option D:	pMOS	
Q24.	Electrostatic discharge for 1pF and 1nC charge	
Option A:	10kV	
Option B:	1mV	
Option C:	1kV	
Option D:	10kV	
Q25.	What is the advantage of using VHDL instead of any other HDL?	
Option A:	Weak Typing	
Option B:	Based on ADA	
Option C:	Portability	
Option D:	Easy to code	

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Question	Correct Option (Enter either 'A' or 'B' or 'C' or 'D')
Q1.	С
Q2.	В
Q3.	В
Q4	В
Q5	С
Q6	С
Q7	A
Q8.	A
Q9.	В
Q10.	С
Q11.	D
Q12.	В
Q13.	A
Q14.	A
Q15.	D
Q16.	A
Q17.	D
Q18.	В
Q19.	A
Q20.	A
Q21.	В
Q22.	С
Q23.	В
Q24.	С
Q25.	С